DATA SHEET

SA5214
Postamplifier with link status indicator

Product specification
Replaces datasheet NE/SA5214 of 1995 Apr 26
IC19 Data Handbook

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Philips
Semiconductors

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Postamplifier with link status indicator SA5214

DESCRIPTION

The SA5214 is a 75MHz postamplifier system designed to accept low level high-speed signals. These signals are converted into a TTL level at the output. The SA5214 can be DC coupled with the previous transimpedance stage using SA5210, SA5211 or SA5212 transimpedance amplifiers. This “system on a chip” features an auto-zeroed first stage with noise shaping, a symmetrical limiting second stage, and a matched rise/fall time TTL output buffer. The system is user-configurable to provide noise filtering, adjustable input thresholds and hysteresis. The threshold capability allows the user to maximize signal-to-noise ratio, insuring a low Bit Error Rate (BER). An Auto-Zero loop can be used to minimize the number of external coupling capacitors to one. A signal absent flag indicates when signals are below threshold. Additionally, the low signal condition forces the overall TTL output to a logical Low level. User interaction with this “jamming” system is available. The SA5214 is packaged in a standard 20-pin surface-mount package and typically consumes 42mA from a standard 5V supply. The SA5214 is designed as a companion to the SA5211/5212 transimpedance amplifiers. These differential preamplifiers may be directly coupled to the post-amplifier inputs. The SA5212/5214 or SA5211/5214 combinations convert nanoamps of photodetector current into standard digital TTL levels.

APPLICATIONS

- Fiber optics
- Communication links in Industrial and/or Telecom environment with high EMI/RFI
- Local Area Networks (LAN)
- Metropolitan Area Networks (MAN)
- Synchronous Optical Networks (SONET)
- RF limiter

PIN CONFIGURATION

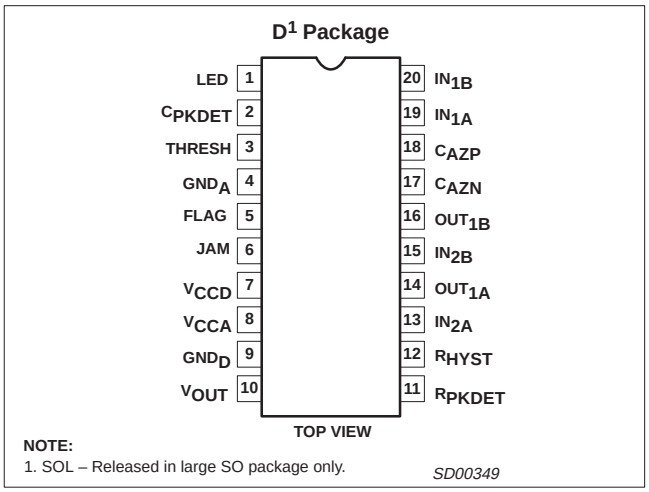


Figure 1. Pin Configuration

FEATURES

- Postamp for the SA5211/5212 preamplifier family
- Wideband operation: typical 75MHz (100MBaud NRZ)
- Interstage filtering/equalization possible
- Single 5V supply
- Low signal flag
- Low signal output disable
- Link status threshold and hysteresis programmable
- LED driver (normally ON with above threshold signal)
- Fully differential for excellent PSRR
- Auto-zero loop for DC offset cancellation
- 2kV ElectroStatic Discharge (ESD) protection

ORDERING INFORMATION

DESCRIPTION	TEMPERATURE RANGE	ORDER CODE	DWG #
20-Pin Plastic Small Outline Large (SOL) Package	-40°C to +85°C	SA5214D	SOT163-1

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNIT
V_{CCA}	Power supply	+6	V
V_{CCD}	Power supply	+6	V
T_A	Operating ambient temperature range	-40 to +85	°C
T_J	Operating junction temperature range	-55 to +150	°C
T_{STG}	Storage temperature range	-65 to +150	°C
P_D	Power dissipation	300	mW
V_{IJ}	Jam input voltage	-0.5 to 5.5	V

PIN DESCRIPTIONS

PIN NO.	SYMBOL	DESCRIPTION
1	LED	Output for the LED driver. Open collector output transistor with 125Ω series limiting resistor. An above threshold signal turns this transistor ON.
2	C_{PKDET}	Capacitor for the peak detector. The value of this capacitor determines the detector response time to the signal, supplementing the internal 10pF capacitor.
3	THRESH	Peak detector threshold resistor. The value of this resistor determines the threshold level of the peak detector.
4	GND_A	Device analog ground pin.
5	FLAG	Peak detector digital output. When this output is LOW, there is data present above the threshold. This pin is normally connected to the JAM pin and has a TTL fanout of two.
6	JAM	Input to inhibit data flow. Sending the pin HIGH forces TTL DATA OUT ON, Pin 10, LOW. This pin is normally connected to the FLAG pin and is TTL-compatible.
7	V_{CCD}	Power supply pin for the digital portion of the chip.
8	V_{CCA}	Power supply pin for the analog portion of the chip.
9	GND_D	Device digital ground pin.
10	V_{OUT}	TTL output pin with a fanout of five.
11	R_{PKDET}	Peak detector current resistor. The value of this resistor determines the amount of discharge current available to the peak detector capacitor, C_{PKDET}.
12	R_{HYST}	Peak detector hysteresis resistor. The value of this resistor determines the amount of hysteresis in the peak detector.
13	IN_{2A}	Non-inverting input to amplifier A2.
14	OUT_{1A}	Non-inverting output of amplifier A1.
15	IN_{2B}	Inverting input to amplifier A2.
16	OUT_{1B}	Inverting output of amplifier A1.
17	C_{AZN}	Auto-Zero capacitor pin (Negative terminal). The value of this capacitor determines the low-end frequency response of the preamp A1.
18	C_{AZP}	Auto-Zero capacitor pin (Positive terminal). The value of this capacitor determines the low-end frequency response of the preamp A1.
19	IN_{1A}	Non-inverting input of the preamp A1.
20	IN_{1B}	Inverting input of the preamp A1.

BLOCK DIAGRAM

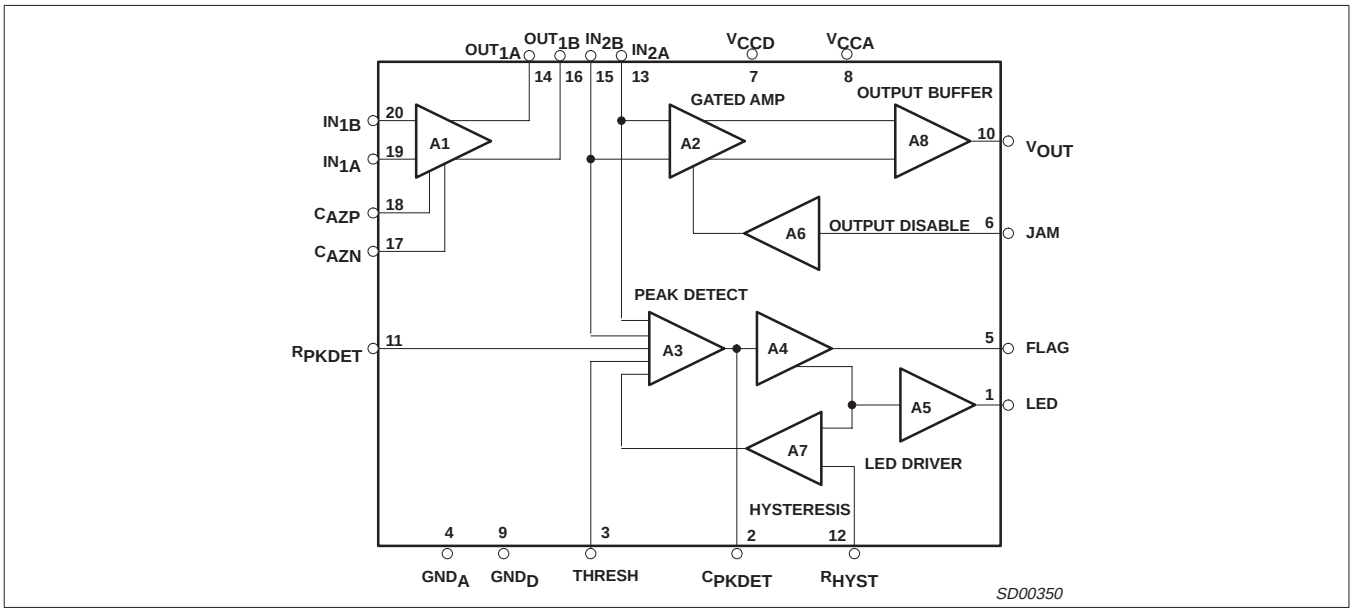


Figure 2. Block Diagram

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	RATING	UNIT
V_{CCA}	Supply voltage	4.75 to 5.25	V
V_{CCD}	Power supply	4.75 to 5.25	V
T_A	Ambient temperature range	-40 to +85	°C
T_J	Operating junction temperature range	-40 to +110	°C
P_D	Power dissipation	250	mW

DC ELECTRICAL CHARACTERISTICS

Min and Max limits apply over the operating temperature range at V_{CCA}=V_{CCD}=+5.0V unless otherwise specified. Typical data applies at V_{CCA}=V_{CCD}=+5.0V and T_A=25°C.

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			Min	Typ	Max	
I_{CCA}	Analog supply current			30	41.2	mA
I_{CCD}	Digital supply current (TTL, Flag, LED)			10	13.5	mA
V_{I1}	A1 input bias voltage (+/- inputs)		3.08	3.4	3.70	V
V_{O1}	A1 output bias voltage (+/- outputs)		3.10	3.8	4.50	V
A_{V1}	A1 DC gain (without Auto-Zero)			30		dB
$A1_{PSRR}$	A1 PSRR (v_{CCA}, V_{CCD})	V_{CCA}=V_{CCD}=4.75 to 5.25V		60		dB
$A1_{CMRR}$	A1 CMRR	ΔV_{CM}=200mV		60		dB
V_{I2}	A2 input bias voltage (+/- inputs)		3.56	3.7	3.86	V
V_{OH}	High-level TTL output voltage	I_{OH}=-200µA	2.4	3.4		V
V_{OL}	Low-level TTL output voltage	I_{OL}=8mA		0.3	0.4	V
I_{OH}	High-level TTL output current	V_{OUT}=2.4V		-40	-24.4	mA
I_{OL}	Low-level TTL output current	V_{OUT}=0.4V	7.0	30		mA
I_{OS}	Short-circuit TTL output current	V_{OUT}=0.0V		-95		mA
V_{THRESH}	Threshold bias voltage	Pin 3 Open		0.75		V
V_{RPKDET}	RPKDET	Pin 11 Open		0.72		V
V_{RHYST}	RHYST bias voltage	Pin 12 Open		0.72		V
V_{IHJ}	High-level jam input voltage		2.0			V
V_{ILJ}	Low-level jam input voltage				0.8	V
I_{IHJ}	High-level jam input current	V_{IJ}=2.7V			30	µA
I_{ILJ}	Low-level jam input current	V_{IJ}=0.4V	-485	-240		µA
V_{OHF}	High-level flag output voltage	I_{OH}=-80µA	2.4	3.8		V
V_{OLF}	Low-level flag output voltage	I_{OL}=3.2mA		0.33	0.4	V
I_{OHF}	High-level flag output current	V_{OUT}=2.4V		-18	-5	mA
I_{OLF}	Low-level flag output current	V_{OUT}=0.4V	3.25	10		mA
I_{SCF}	Short-circuit flag output current	V_{OUT}=0.0V	-61	-40	-26	mA
I_{LEDH}	LED ON maximum sink current	V_{LED}=3.0V	8	22	80	mA

AC ELECTRICAL CHARACTERISTICS

Min and Max limits apply over the operating temperature range at V_{CCA} = V_{CCD} = +5.0V unless otherwise specified. Typical data applies at V_{CCA} = V_{CCD} = +5.0V and T_A = 25°C.

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			Min	Typ	Max	
f_{OP}	Maximum operating frequency	Test circuit	60	75		MHz
BW_{A1}	Small signal bandwidth (differential OUT_1/IN_1)	Test circuit		75		MHz
V_{INH}	Maximum Functional A1 input signal (single ended)	Test Circuit		1.6		V_{P-P}
V_{INL}	Minimum Functional A1 input signal (single ended)	Test CIrcuit[1]		12		mV_{P-P}
R_{IN1}	Input resistance (differential at IN_1)			1200		Ω
C_{IN1}	Input capacitance (differential at IN_1)			2		pF
R_{IN2}	Input resistance (differential at IN_2)			1200		Ω
C_{IN2}	Input capacitance (differential at IN_2)			2		pF
R_{OUT1}	Output resistance (differential at OUT_1)			25		Ω
C_{OUT1}	Output capacitance (differential at OUT_1)			2		pF
V_{HYS}	Hysteresis voltage	Test circuit		3		mV_{P-P}
V_{THR}	Threshold voltage range (FLAG ON)	Test circuit, @ 50MHz R_{RHYST}=5k R_{THRESH}=47k		12		mV_{P-P}
t_{TLH}	TTL Output Rise Time 20% to 80%	Test Circuit		1.3		ns
t_{THL}	TTL Output Fall Time 80% to 20%	Test Circuit		1.2		ns
t_{RFD}	t_{TLH}/t_{THL} mismatch			0.1		ns
t_{PWD}	Pulse width distortion of output	$50mV_{P-P}$, 1010. . .input Distortion= $\frac{T_H-T_L}{T_H+T_L}$ 10^2		2.5		%

NOTES:

1. The SA5214 is capable of detecting a much lower input level. Operation under $12mV_{P-P}$ cannot be guaranteed by present day automatic testers.

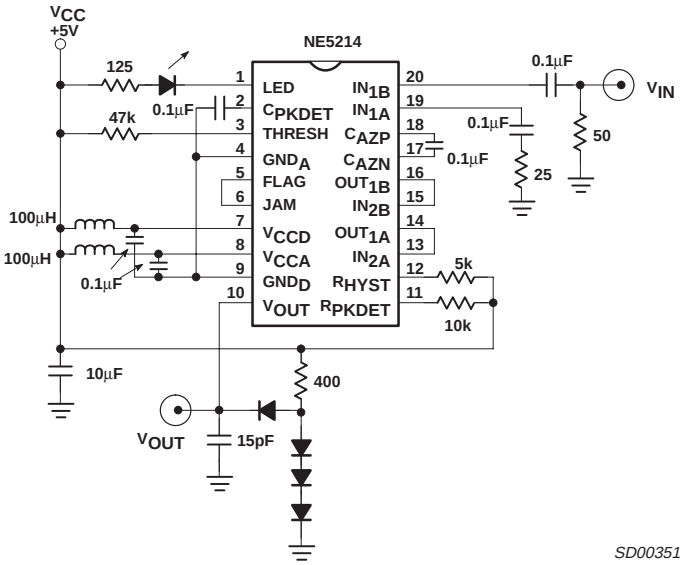


Figure 3. AC Test Circuit

TYPICAL PERFORMANCE CHARACTERISTICS

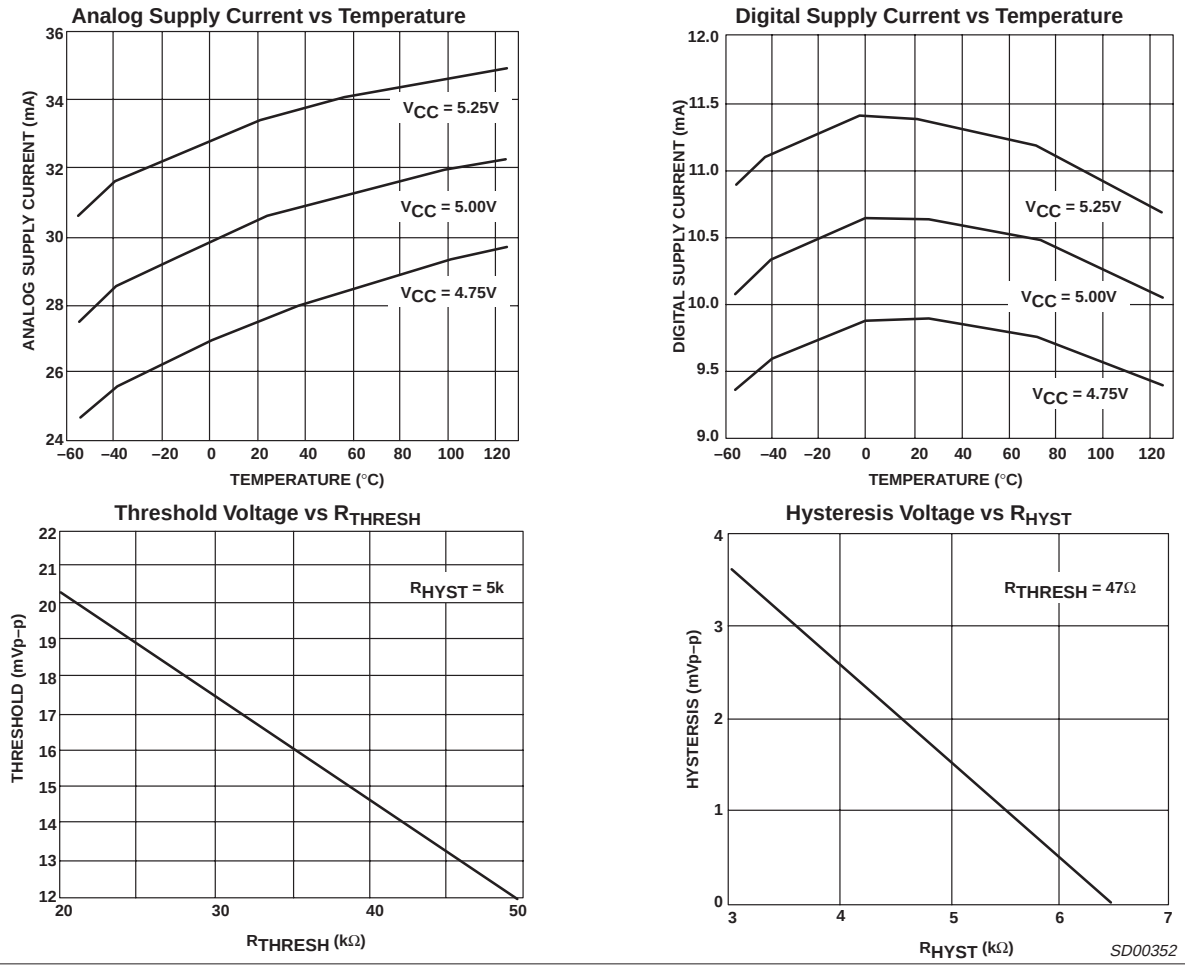
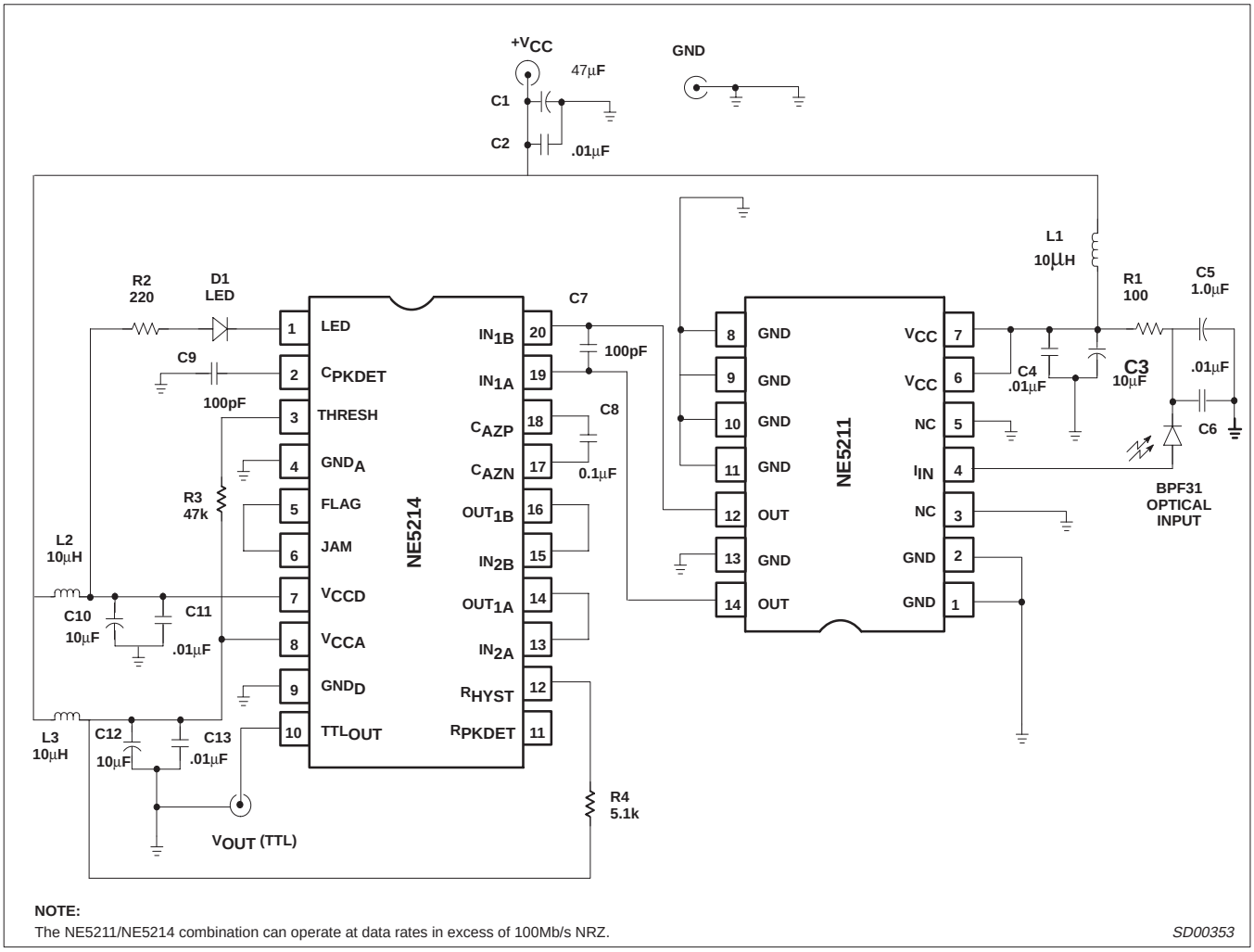


Figure 4. Typical Performance Characteristics



NOTE:
The NE5211/NE5214 combination can operate at data rates in excess of 100Mb/s NRZ.

SD00353

Figure 5. A 50Mb/s Fiber Optic Receiver

THEORY OF OPERATION AND APPLICATION INFORMATION

The SA5214 postamplifier system is a highly integrated chip that provides up to 60dB of gain at 60MHz, to bring mV level signals up to TTL levels.

The SA5214 contains eight amplifier blocks (see Block Diagram). The main signal path is made up of a cascade of limiting stages: A1, A2 and A8. The A3-A4-A7 path performs a wideband full-wave rectification of the input signal with adjustable hysteresis and decay times. It outputs a TTL HIGH on the “FLAG” output (Pin 5) when the input is below a user adjustable threshold. An on-chip LED driver turns the external LED to the ON state when the input signal is above the threshold. In a typical application the “FLAG” output is tied back to the “JAM” input; this forces the TTL data OUT into a LOW state when no signal is present at the input.

An auto zero loop allows the SA5214 to be directly connected to a transimpedance amplifier such as the SA5210, SA5211, or SA5212 without coupling capacitors. This auto-zero loop cancels the transimpedance amplifier’s DC offset, the SA5214 A1 offset, and the data-dependent offset in the PIN diode/transimpedance amplifier combination. For more information on the SA5214 Theory of Operation, please refer to paper titled “A Low Cost 100 MBaud Fiber-Optic Receiver” by W. Mack et al.

A typical application of the SA5214 postamplifier is depicted in Figure 5. The system uses the SA5211 transimpedance amplifier which has a 28k differential transimpedance gain and a -3dB bandwidth of 140MHz. This typical application is optimized for a 50 Mb/s Non Return to Zero (NRZ) bit stream.

As the system’s gain bandwidth product is very high, it is crucial to employ good RF design and printed circuit board layout techniques to prevent the system from becoming unstable.

For more information on this application, please refer to AB 1432.

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Due to the limitations in testing high frequency and other parameters at the die level, and the fact that die electrical characteristics may shift after packaging, die electrical parameters are not specified and die are not guaranteed to meet electrical characteristics (including temperature range) as noted in this data sheet which is intended only to specify electrical characteristics for a packaged device.

All die are 100% functional with various parametrics tested at the wafer level, at room temperature only (25°C), and are guaranteed to be 100% functional as a result of electrical testing to the point of wafer sawing only. Although the most modern processes are utilized for wafer sawing and die pick and place into waffle pack carriers, it is impossible to guarantee 100% functionality through this process. There is no post waffle pack testing performed on individual die.

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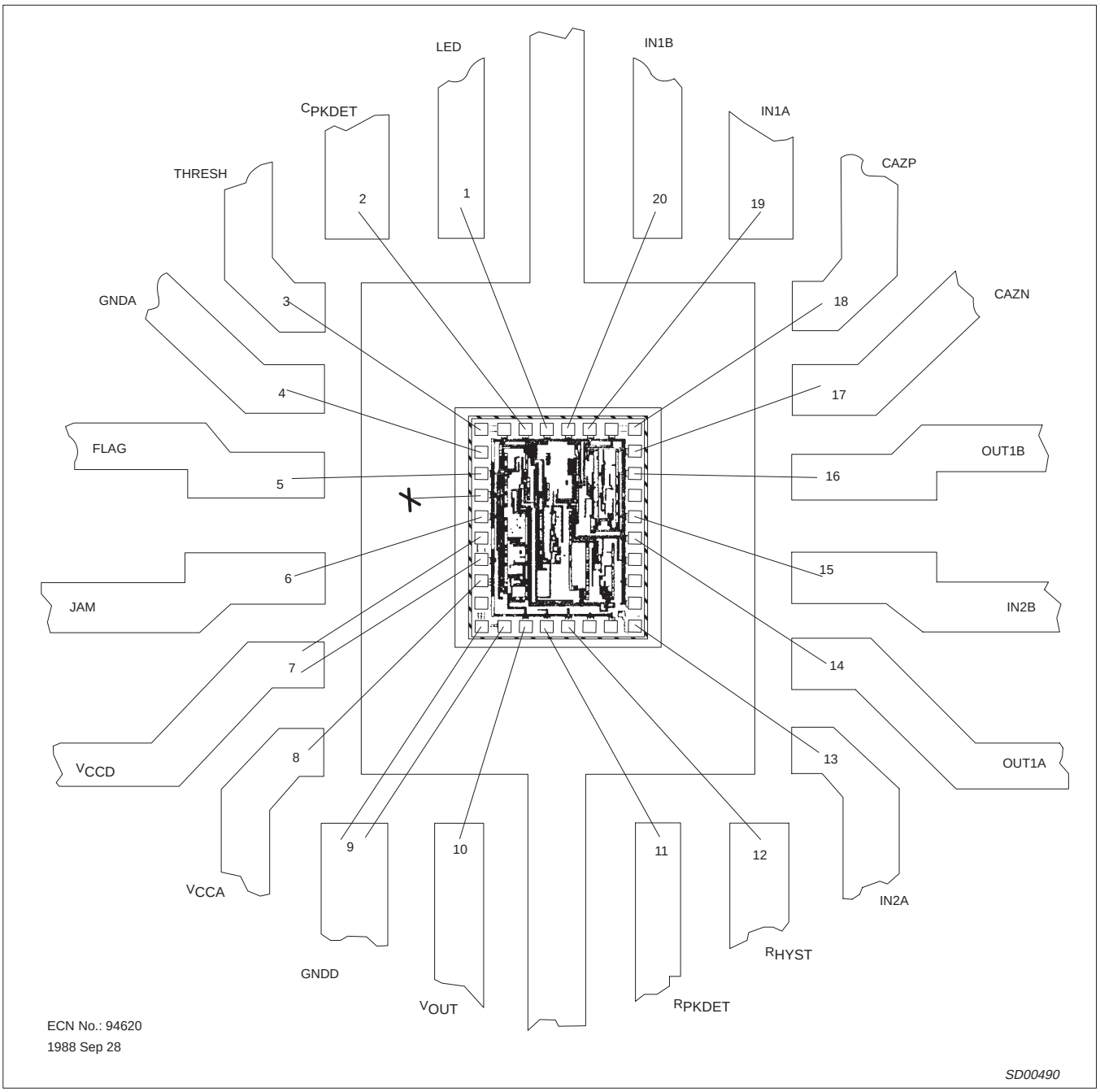
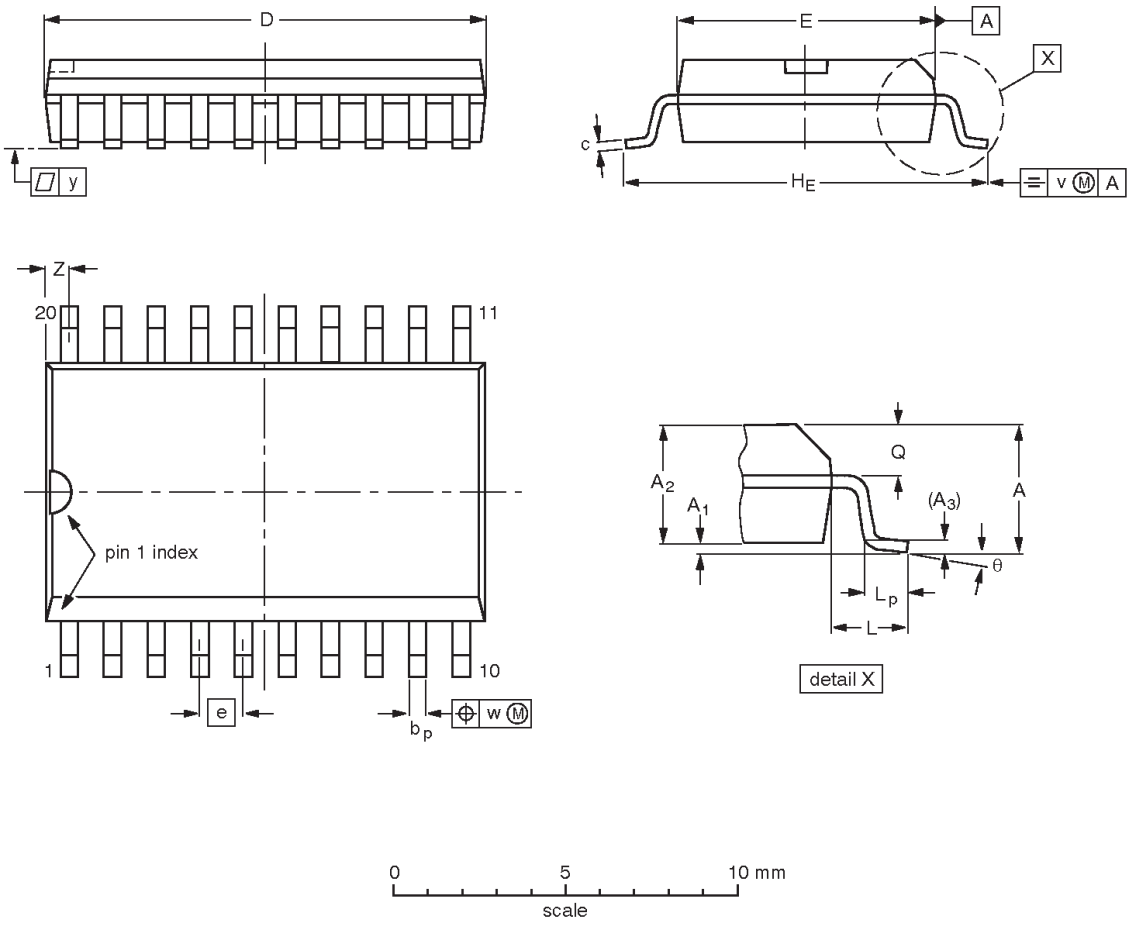


Figure 6. SA5214 Bonding Diagram

SO20: plastic small outline package; 20 leads; body width 7.5 mm **SOT163-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	2.65	0.30 0.10	2.45 2.25	0.25	0.49 0.36	0.32 0.23	13.0 12.6	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8^o 0^o
inches	0.10	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.51 0.49	0.30 0.29	0.050	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT163-1	075E04	MS-013AC				~~95-01-24~~ 97-05-22

Postamplifier with link status indicator SA5214

Data sheet status

Data sheet status	Product status	Definition [1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make chages at any time without notice in order to improve design and supply the best possible product.
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[1] Please consult the most recently issued datasheet before initiating or completing a design.

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